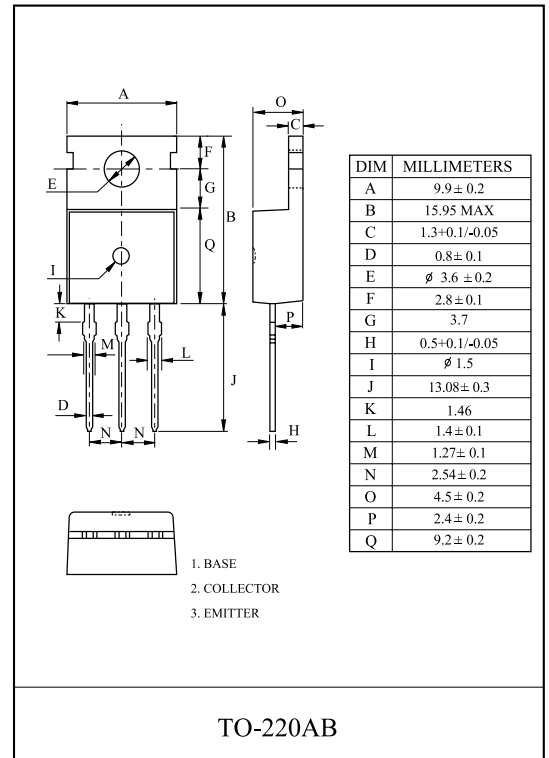


HIGH VOLTAGE AND HIGH RELIABILITY
HIGH SPEED SWITCHING, WIDE SOA

MAXIMUM RATING (Ta=25 °C)

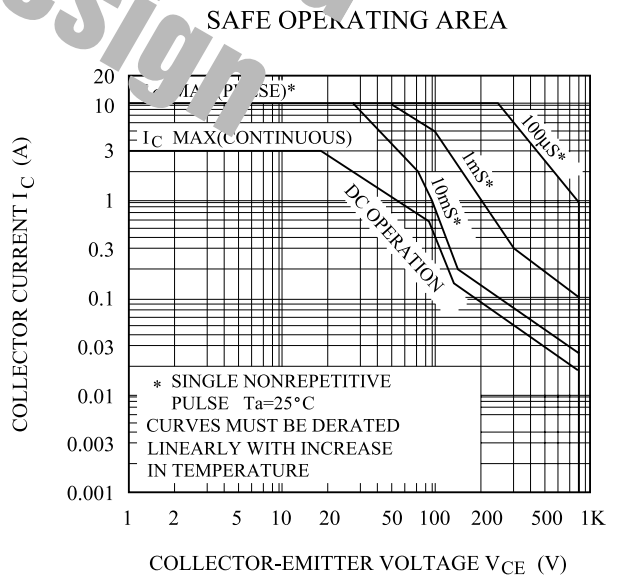
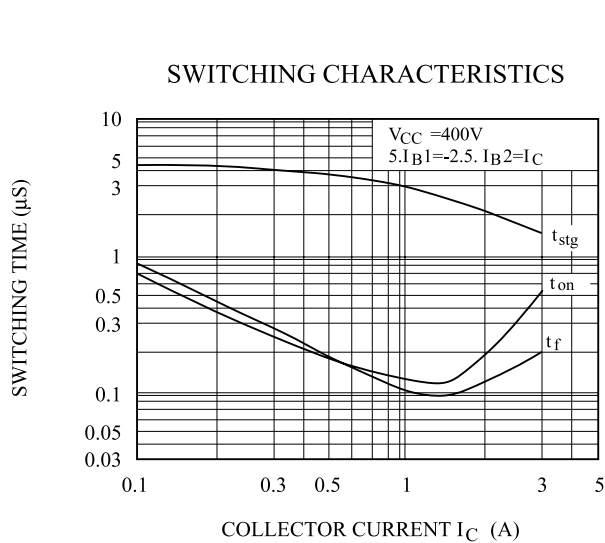
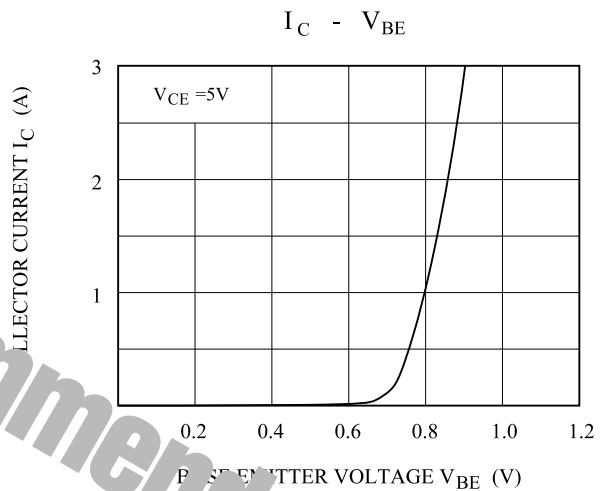
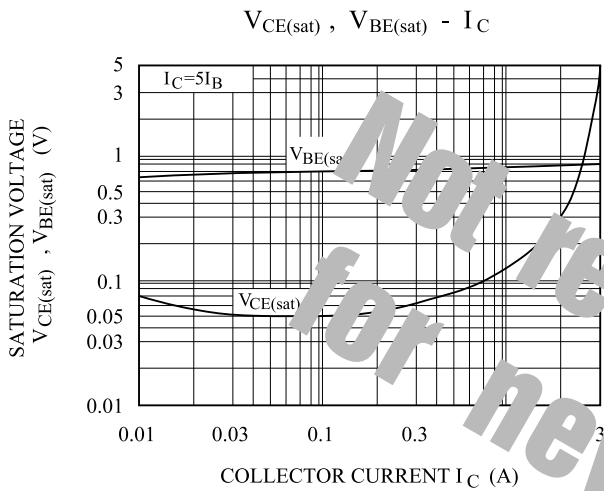
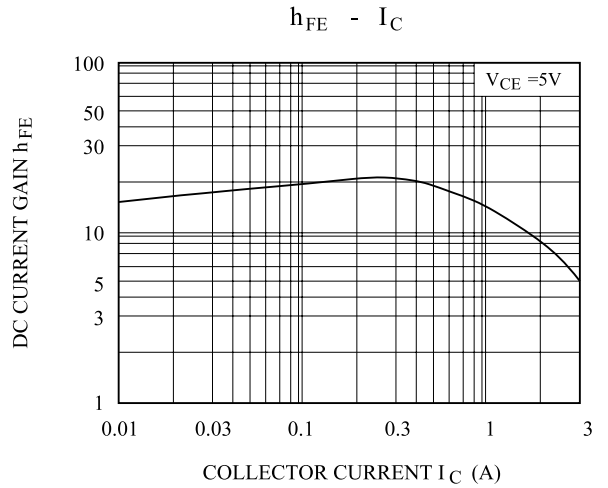
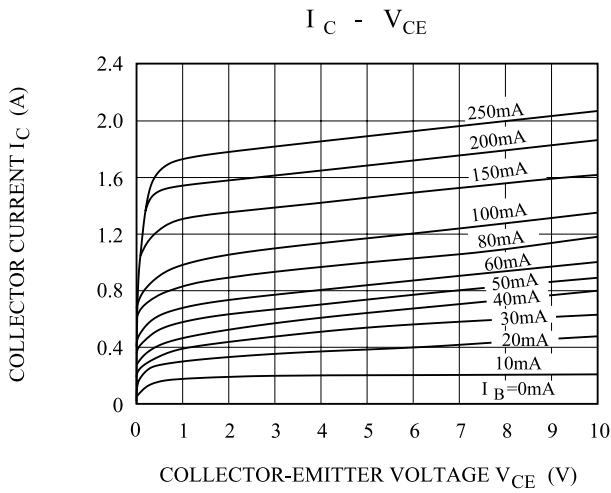
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	1100	V
Collector-Emitter Voltage		V_{CEO}	800	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	I_C	3	A
	Pulse	I_{CP}	10	
Base Current		I_B	1.5	A
Collector Power Dissipation (Tc=25 °C)		P_C	50	W
Junction Temperature		T_j	150	
Storage Temperature Range		T_{stg}	-55 150	



ELECTRICAL CHARACTERISTICS (Ta=25 °C)

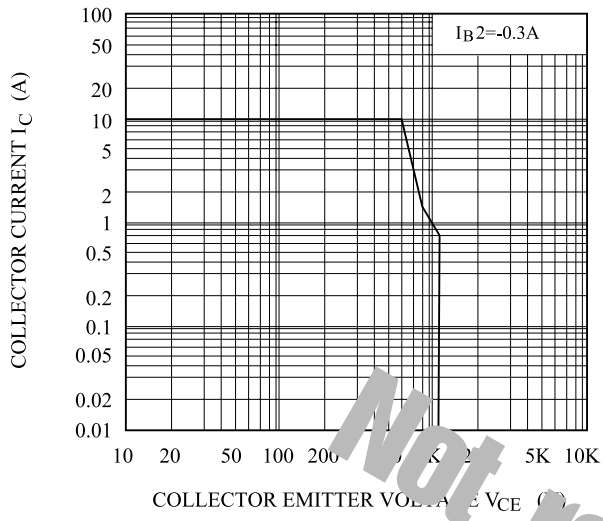
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB}=800V, I_E=0$	-	-	10	µA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	10	µA
Collector-Emitter Sustaining Voltage		$V_{CEX(SUS)}$	$I_C=1.5A, I_B=-I_B=0.3A$ $L=2mH, Clamped$	800	-	-	V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=1.5A, I_B=0.2A$	-	-	2	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C=1.5A, I_B=0.3A$	-	-	1.5	V
DC Current Gain	$h_{FE}(1)$ (Note)		$V_{CE}=5V, I_C=0.2A$	15	-	40	
	$h_{FE}(2)$		$V_{CE}=5V, I_C=1A$	8	-	-	
Collector-Base Breakdown Voltage		BV_{CBO}	$I_C=1mA, I_E=0$	1100	-	-	V
Collector-Emitter Breakdown Voltage		BV_{CEO}	$I_C=5mA, R_{BE}=\infty$	800	-	-	V
Emitter-Base Breakdown Voltage		BV_{EBO}	$I_E=1mA, I_C=0$	7	-	-	V
Collector Output Capacitance		C_{ob}	$V_{CB}=10V, f=1MHz, I_E=0$	-	60	-	pF
Transition Frequency		f_T	$V_{CE}=10V, I_C=0.2A$	-	15	-	MHz
Switching Time	Turn On Time	t_{on}	<p>$I_{B1}=0.4A, I_{B2}=-0.8A$ DUTY CYCLE ≤ 1% $V_{CC}=400V$</p>	-	-	0.5	µs
	Storage Time	t_{stg}		-	-	3	
	Fall Time	t_f		-	-	0.3	

Note : $h_{FE}(1)$ Classification R:15 30, O:20 40

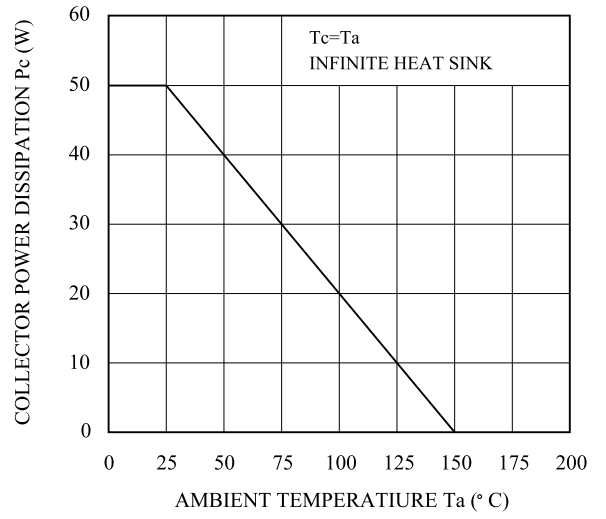


KTC5027

REVERSE BIAS SAFE OPERATING AREA



$P_c - T_a$



Not recommended
for new design